Product data sheet

1. General description

Hyperfast power diode in a 2-lead IITO220 plastic package.

2. Features and benefits

- · Isolated plastic package
- Low leakage current
- · Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter Conditions			Va	lues		Unit
Absolute maximum rating							
V_{RRM}	repetitive peak reverse voltage		600				V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 90 °C; square-wave pulse Fig. 1; Fig. 2; Fig. 3	30				А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 90 °C; square-wave pulse	60			А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	e; 200			А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220		Α		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	$I_F = 30 \text{ A}; T_j = 150 \text{ °C}; Fig. 6$ - 1.38		1.8	V		
Dynamic	Dynamic characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	-	35	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	Α	anode		K — A
mb	n.c.	mounting base; isolated	1 2 2 IITO220-2L	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC30Y-600P	IITO220-2L	BYC30Y-600PQ	Tube	50	IITO220E-2L	03-Mar-2020

7. Marking

Table 4. Marking codes

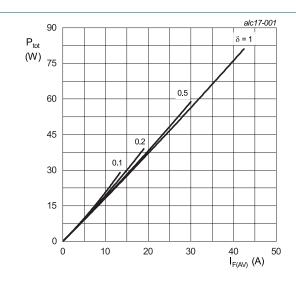
Type number	Marking codes
BYC30Y-600P	BYC30Y
	600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	$δ = 0.5$; $T_{mb} \le 90$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	30	Α
I _{FRM}	repetitive peak forward current	δ = 0.5; t_p = 25 μs; T_{mb} ≤ 90 °C; square-wave pulse	60	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	200	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.797 \text{ V; } R_{\text{s}} = 0.0027 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

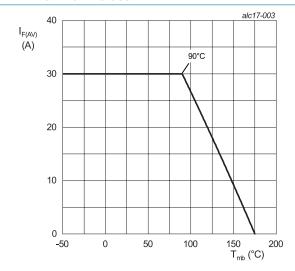
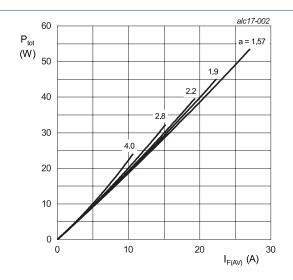


Fig. 3. Forward current as a function of mounting base temperature; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.797 V; R_s = 0.0027 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

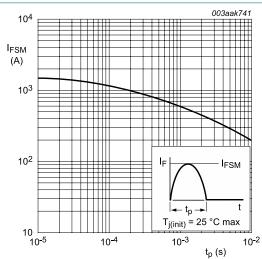
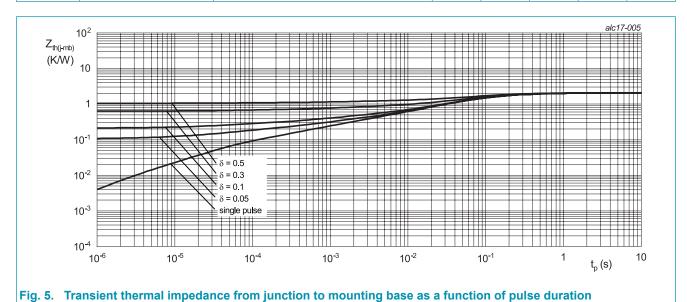


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	2.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



10. Isolation characteristics

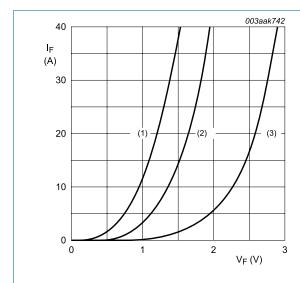
Table 7. Isolation characteristics

S	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
٧	/isol(RMS)	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C	Sisol	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	M	in T	ур	Max	Unit
Static cha	racteristics						
V _F	forward voltage	I _F = 30A; T _j = 25 °C; <u>Fig. 6</u>	-	2		2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.	.38	1.8	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-		10	μΑ
		V _R = 600 V; T _j = 150 °C	-	-		1	mA
Dynamic (characteristics						
Q _r recovere	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_J = 25 \text{ °C}; Fig. 7$	-	5	0	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_J = 125 ^{\circ}\text{C}; Fig. 7$	-	2	80	-	nC
t _{rr} rever	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-		35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/µs};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	-		35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	7	0	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	3	.5	-	А
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	7.	.6	-	Α



(1) T_j = 150 °C; typical values (2) $T_j = 150$ °C; maximum values

(3) $T_j = 25$ °C; maximum values $V_o = 1.797 \text{ V}; R_s = 0.0027 \Omega$

Fig. 6. Forward current as a function of forward voltage

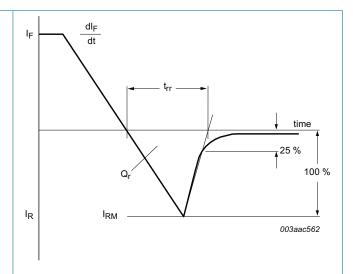
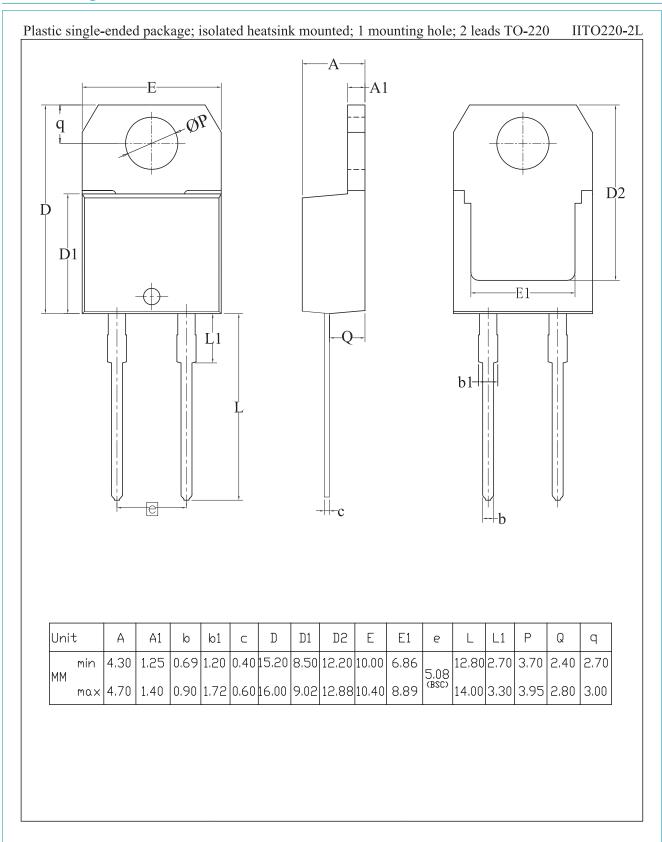


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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